

/ Descriptions

TO-220F NPN Silicon NPN transistor in a TO-220F Plastic Package.

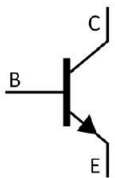
/ Features

, KTA1046
Low saturation voltage, complementary to KTA1046.

/ Applications

General Purpose Application.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

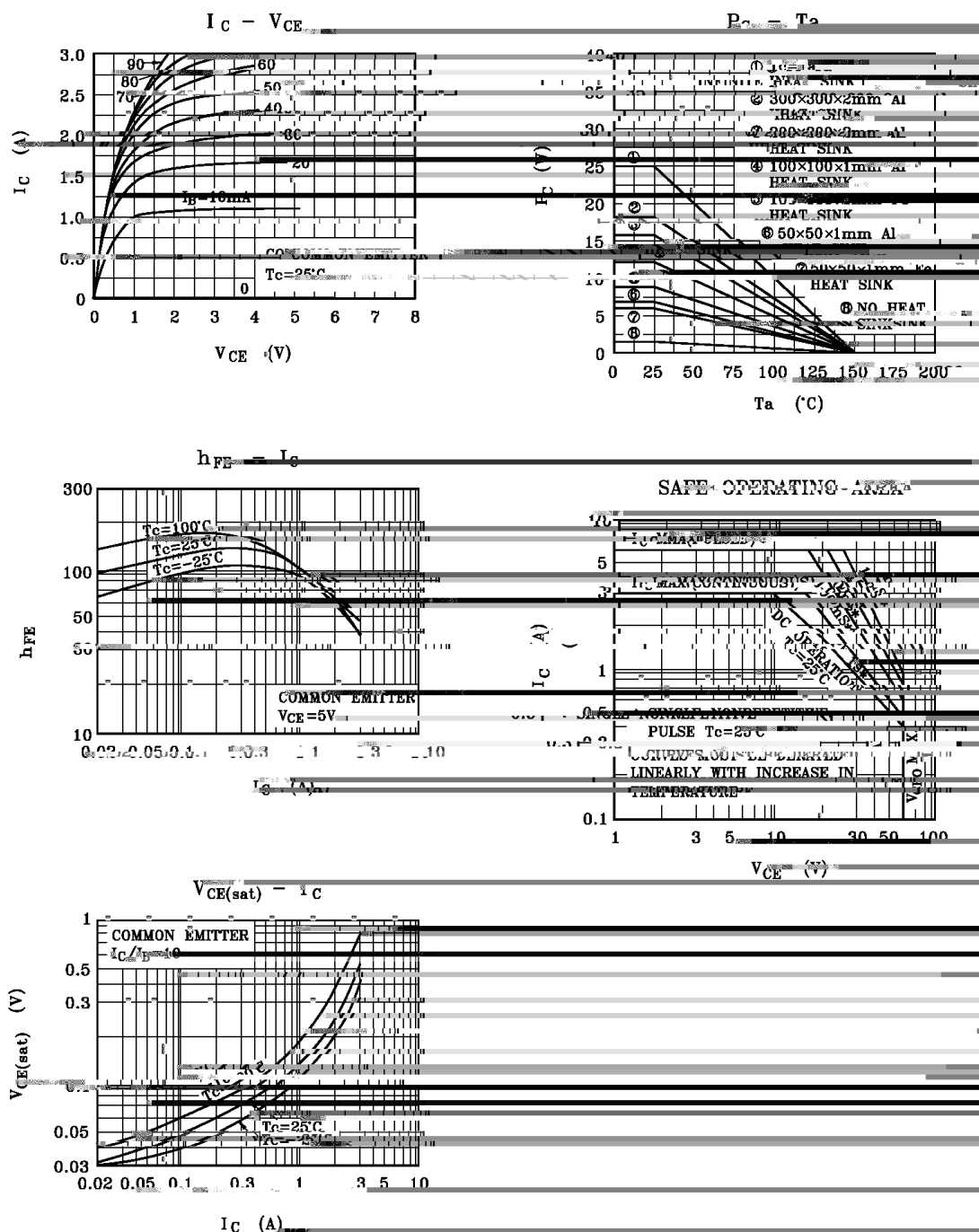
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Y	GR
h_{FE} Range	100~200	150~300

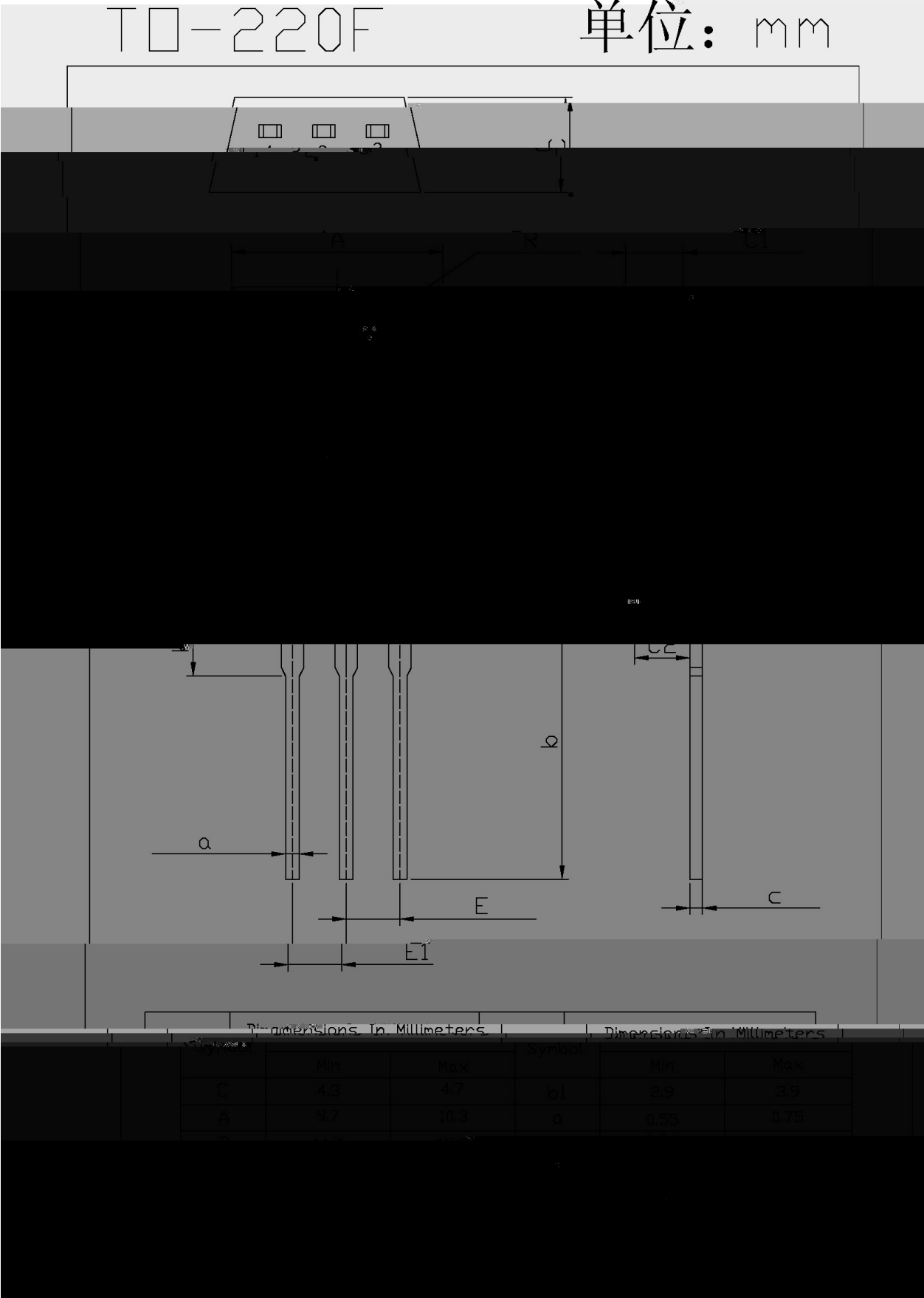
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Base Current	I_B	500	mA
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_{C(T_c=25^\circ C)}$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=50mA$ $I_B=0$	60			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			100	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=7.0V$ $I_C=0$			100	A
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=500mA$	100		300	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.0A$ $I_B=200mA$		0.25	1.0	V

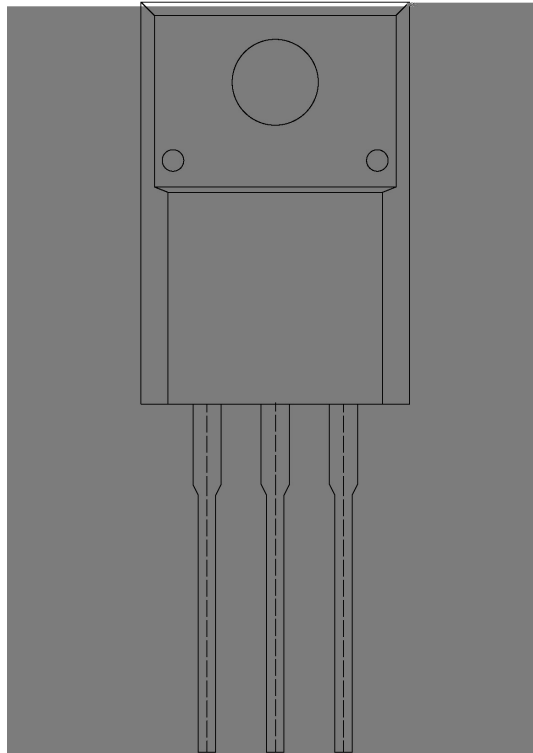
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

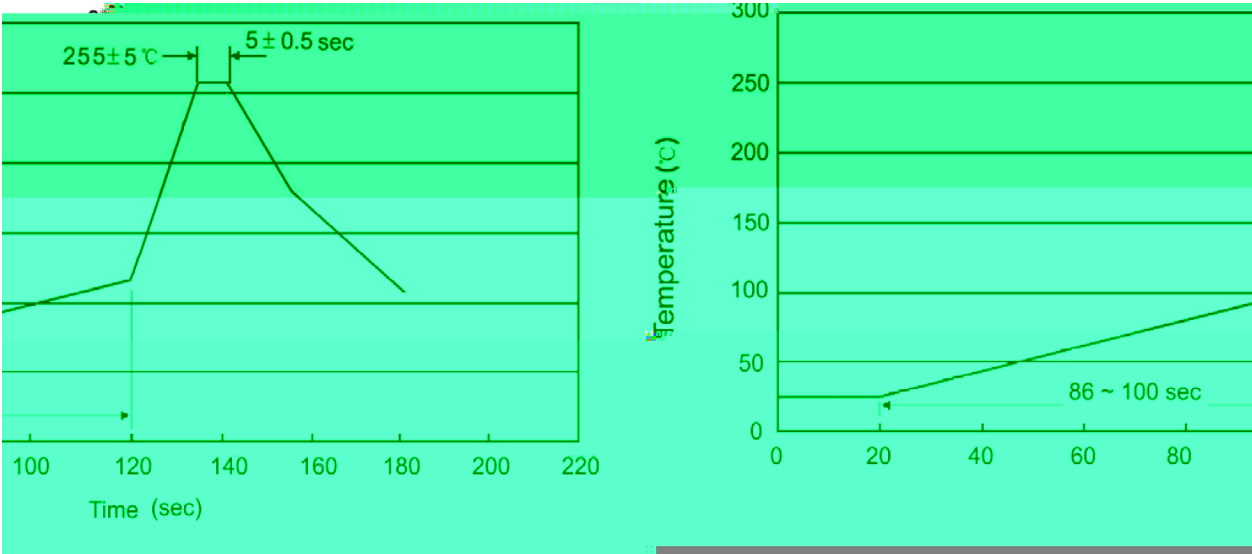
C2026

Y: h_{FE}

Note:

BR: Company Code.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10 /sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

/ TU